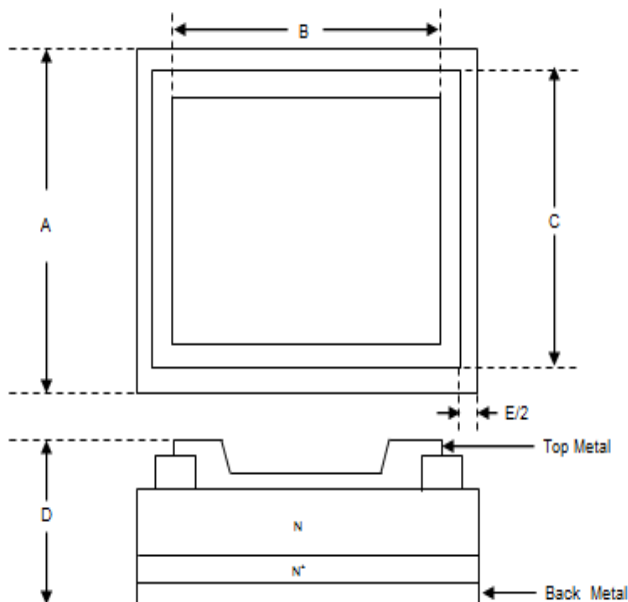


Planar Schottky Barrier Diode Wafer (PSBD)



Item	Dimensions	
	um	mil
Die Size (A)	260	10.2
Top Metal Pad Size (B)	214	8.42
Passivation Seal (C)	234	9.21
Wafer Thickness (D)	150	6
Scribe Line Width (E)	40	1.57
Other Informations		
Wafer Size	6"	
Gross Die	243000	
Top Metal	TiW/Al 0.2/ 3um	
Back Metal	TiNi-Ag-Sn 0.2-0.8-1.4	

Electrical Characteristics @TA=25°C

Item	Symbol	Spec. Limit	Typical	Unit
Maximum Repetitive Peak Reverse Voltage @0.2mA	V_{RRM}	35	55	V
Maximum Average Forward Rectified Current	I_o	0.2	-	A
Forward Voltage Drop, @ $I_F=1mA$ @ $I_F=10mA$ @ $I_F=100mA$ @ $I_F=200mA$	V_F	0.32 0.40 0.55 0.69	0.29 0.52 0.66	V
Maximum Reverse Current at Rated $V_{RRM}=30V$	I_R	0.5	0.1	μA
Peak Forward Surge Current, 1s	I_{FSM}	0.5		A
Operating Temperature Range	T_J	-50 to +125	-	°C
Storage Temperature Range	T_{STG}	-50 to +125	-	°C